

COMPLIANT



Low-Voltage Dual SPST Analog Switch

DESCRIPTION

The DG9232/9233 is a single-pole/single-throw monolithic CMOS analog device designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 35 ns, t_{OFF} : 20 ns), low on-resistance ($r_{DS(on)}$: 20 Ω) and small physical size, the DG9232/9233 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9232/9233 is built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per Method 3015.7 is 2000 V. An epitaxial layer prevents latchup. Break-before -make is guaranteed for DG9232/9233.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

BENEFITS

- Reduced Power Consumption
- · Simple Logic Interface
- High Accuracy
- Reduce Board Space

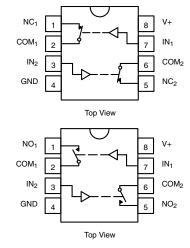
FEATURES

- Low Voltage Operation (+ 2.7 to + 5 V)
- Low On-Resistance $r_{DS(on)}$: 20 Ω
- Fast Switching t_{ON}: 35 ns, t_{OFF}: 20 ns
- Low Leakage I_{COM(on)}: 200 pA max
- Low Charge Injection Q_{INJ}: 1 pC
- · Low Power Consumption
- TTL/CMOS Compatible
- ESD Protection > 2000 V (Method 3015.7)
- Available in MSOP-8 and SOIC-8

APPLICATIONS

- · Battery Operated Systems
- · Portable Test Equipment
- · Sample and Hold Circuits
- · Cellular Phones
- Communication Systems
- · Military Radio
- PBX, PABX Guidance and Control Systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE - DG9232				
Logic	Switch			
0	ON			
1	OFF			

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

TRUTH TABLE - DG9233			
Logic	Switch		
0	OFF		
1	ON		

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

RING INFORMATIO	N	
Temp Range	Package	Part Number
		DG9232DY
		DG9232DY-E3
		DG9232DY-T1
- 40 to 85 °C	SOIC-8	DG9232DY-T1-E3
		DG9233DY
		DG9233DY-E3
		DG9233DY-T1
		DG9233DY-T1-E3
	MSOP-8	DG9232DQ-T1-E3
	IVISOF -0	DG9233DQ-T1-E3

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

Document Number: 70837 S-71009–Rev. E, 14-May-07



ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND		- 0.3 to + 13	V		
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	V		
Continuous Current (Any terminal)		± 20	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 40	IIIA		
ESD (Method 3015.7)		> 2000	V		
Storage Temperature	D Suffix - 65 to		°C		
Power Dissipation (Packages) ^b	8-Pin Narrow Body SOIC ^c	400	mW		

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 6.5 mW/°C above 70 °C.

		Test Conditions Otherwise Unless Specified		D Suffix - 40 to 85 °C			
Parameter	Symbol	$V+ = 3 \text{ V}, \pm 10 \text{ %}, V_{IN} = 0.8 \text{ V or } 2.4 \text{ V}^e$	Temp ^a	Min ^c	Typ ^b	Max ^c	Uni
Analog Switch	Symbol	v+ - 0 v, ± 10 /0, v _{IN} - 0.0 v 01 2.4 v	remp	IVIII	тур	wax	Uni
			F	1 0 1		1 0	V
Analog Signal Range ^d	V _{ANALOG}		Full	0		3	V
Drain-Source On-Resistance	r _{DS(on)}	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $V_{T} = 2.7 \text{ V}$	Room		30	50 80	
	` ′	I _{COM} = 5 mA	Full				_
r _{DS(on)} Match ^d	$\Delta r_{DS(on)}$	V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room		0.4	2	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V_{NO} or $V_{NC} = 1$ and 2 V	Room		4	8	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	V_{NO} or $V_{NC} = 1 \text{ V/2 V}$, $V_{COM} = 2 \text{ V/1 V}$	Room Full	- 100 - 5000	5	100 5000	pA
COM Off Leakage Current ^g	I _{COM(off)}	$V_{COM} = 1 \text{ V/2 V}, V_{NO} \text{ or } V_{NC} = 2 \text{ V/1 V}$	Room Full	- 100 - 5000	5	100 5000	
Channel-On Leakage Current ^g	I _{COM(on)}	$V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/2 V}$	Room Full	- 200 - 10000	10	200 10000	
Digital Control							
Input Current	I _{INL} or I _{INH}		Full		1		μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}		Room Full		50	120	
		V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room		20	200 50	ns
Turn-Off Time	t _{OFF}		Full		20	120	
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$	Room		1	5	рС
Off-Isolation	OIRR		Room		- 74		<u> </u>
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 90		dB
NC and NO Capacitance	C _{S(off)}		Room		7		
Channel-On Capacitance	C _{COM(on)}	f = 1 MHz	Room		20		pF
COM-Off Capacitance	C _{COM(off)}		Room		13		1
Power Supply	20(0)					1	
Positive Supply Range	V+			2.7		12	V
Power Supply Current	I+	$V+ = 3.3 \text{ V}, V_{IN} = 0 \text{ or } 3.3 \text{ V}$				1	μA

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 5-V leakage tests, not production tested.



Parameter		Test Conditions Otherwise Unless Specified $V+ = 5 V, \pm 10 \%, V_{IN} = 0.8 V \text{ or } 2.4 V^{e}$		D Suffix - 40 to 85°C			
	Symbol		Temp ^a	Min ^c	Typ ^b	Max ^c	Unit
Analog Switch							
Analog Signal Range ^d	V _{ANALOG}		Full	0		5	V
Drain-Source On-Resistance	r _{DS(on)}	V_{NO} or $V_{NC} = 3.5 \text{ V}, V_{+} = 4.5 \text{ V}$ $I_{COM} = 5 \text{ mA}$	Room Full		20	30 50	
r _{DS(on)} Match ^d	$\Delta r_{DS(on)}$	V_{NO} or $V_{NC} = 3.5 \text{ V}$	Room		0.4	2	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V_{NO} or $V_{NC} = 1$, 2 and 3 V	Room		2	6	-
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	V_{NO} or V_{NC} = 1 V/4 V, V_{COM} = 4 V/1 V	Room Full	- 100 - 5000	10	100 5000	pA
COM Off Leakage Current	I _{COM(off)}	$V_{COM} = 1 \text{ V/4 V}, V_{NO} \text{ or } V_{NC} = 4 \text{ V/1 V}$	Room Full	- 100 - 5000	10	100 5000	
Channel-On Leakage Current	I _{COM(on)}	$V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/4 V}$	Room Full	- 200 - 10000		200 10000	
Digital Control							•
Input Current	I _{INL} or I _{INH}		Full		1		μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V_{NO} or $V_{NC} = 3.0 \text{ V}$	Room Full		35	75 150	ns
Turn-Off Time	t _{OFF}		Room Full		20	50 100	113
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$	Room		2	5	рC
Off-Isolation	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 74		dB
Crosstalk	X _{TALK}	11L = 30 32, OL = 3 p1, 1 = 1 Wi112	Room		- 90		ub
NC and NO Capacitance	C _(off)	f = 1 MHz	Room		7		
Channel-On Capacitance	C _{D(on)}		Room		20		pF
COM-Off Capacitance	C _{D(off)}		Room		13		
Power Supply							•
Positive Supply Range	V+			2.7		12	V
Power Supply Current	l+	V+ = 5.5 V, V _{IN} = 0 or 5.5 V				1	μA

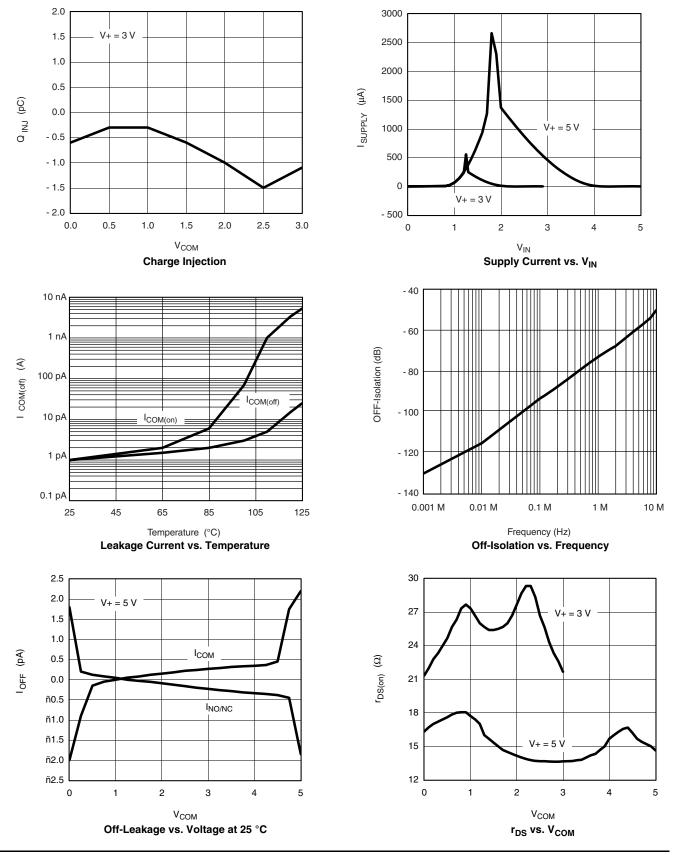
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
 c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

VISHAY

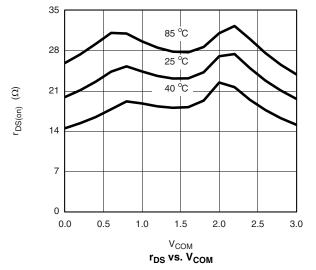
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

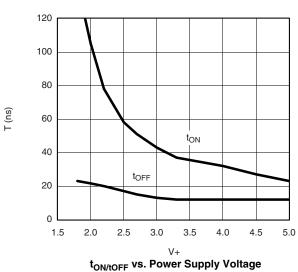


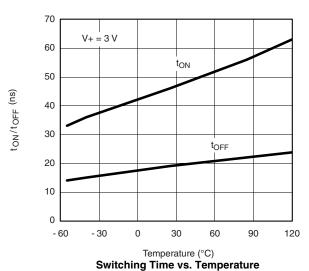


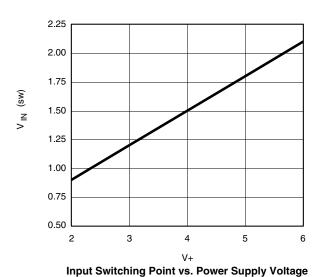


TYPICAL CHARACTERISTICS $T_A = 25~^{\circ}C$, unless otherwise noted



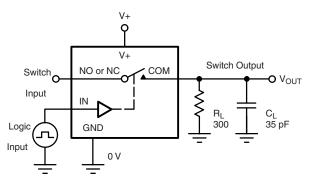






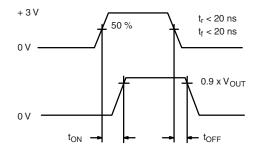
TEST CIRCUITS





Switch Output

Logic Input



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

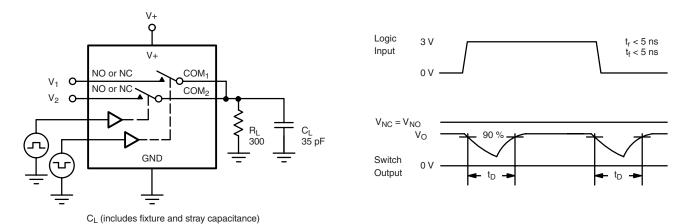
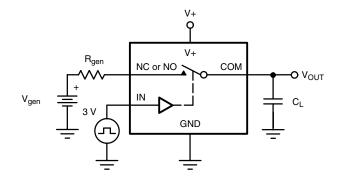
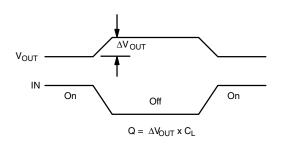


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



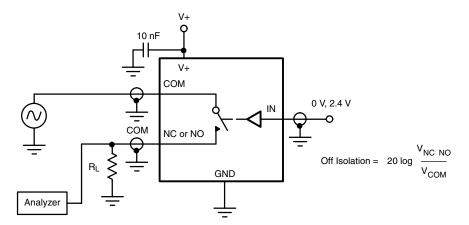


Figure 4. Off-Isolation

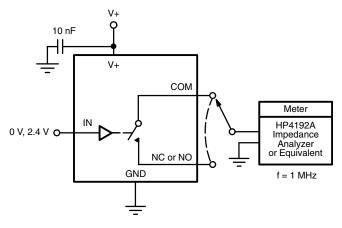


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70837.

Document Number: 70837 S-71009–Rev. E, 14-May-07

Legal Disclaimer Notice



Vishay

Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.

Document Number: 91000 www.vishay.com
Revision: 08-Apr-05 1